TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOS III)

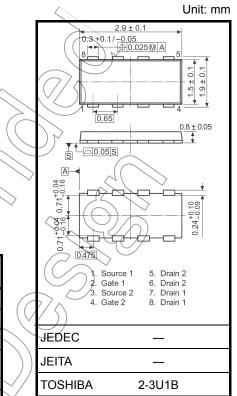
# **TPCF8301**

## Notebook PC Applications Portable Equipment Applications

- Low drain-source ON resistance:  $RDS(ON) = 72 m\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 4.7 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = -10 \ \mu A \ (max) \ (V_{DS} = -20 \ V)$ 
  - Enhancement model:  $V_{th} = -0.5$  to -1.2 V ( $V_{DS} = -10$  V,  $I_D = -200 \mu A$ )

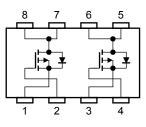
## Absolute Maximum Ratings (Ta = 25°C)

Cha	Symbol	Rating	Unit	
Drain-source voltag	VDSS	20	V	
Drain-gate voltage	VDGR	-20	V	
Gate-source voltag	VGSS	<u>+8</u>	X	
Drain current	DC (Note 1)	<u>t</u> D	> -2.7	$\langle \rangle$
	Pulse (Note 1)		-10.8	A
Drain power	Single-device operation (Note 3a)	PD (1)	1.35 <	
dissipation (t = 5 s) (Note 2a)	Single-device value at dual operation (Note 3b)	PD (2)	1.12	×
Drain power dissipation (t = 5 s) (Note 2b)	Single-device operation (Note 3a)	P <sub>D (1)</sub>	0.53	$\rightarrow$
	Single-device value at dual operation (Note 3b)	P <sub>D</sub> (2)	0.33	
Single pulse avalar	nche energy (Note 4)	EAS	1,2	mJ
Avalanche current	$\sim$	IAR	-1.35	А
Repetitive avalance Single-device value	EAR	0.11	mJ	
Channel temperatu	Tch	150	°C	
Storage temperatu	re-range	T <sub>stg</sub>	-55~150	°C



Weight: 0.011 g (typ.)

## **Circuit Configuration**



Note: Using continuously under neavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

#### **Thermal Characteristics**

Chara	Symbol	Max	Unit		
Thermal resistance, channel to ambient	Single-device operation (Note 3a) Rth (ch-a) (1) 92		92.6	°C/W	
(t = 5 s) (Note 2a)	Single-device value at dual operation (Note 3b)	R <sub>th (ch-a) (2)</sub>	111.6	0/10	
Thermal resistance, channel to ambient	Single-device operation (Note 3a)	R <sub>th (ch-a)</sub> (1)	235.8	°C/W	
(t = 5 s) (Note 2b)	Single-device value at dual operation (Note 3b)	R <sub>th (ch-a) (2)</sub>	378.8	0/10	

Note: (Note 1), (Note 2), (Note 3), (Note 4), (Note 5) and (Note 6): See the next page.

This transistor is an electrostatic-sensitive device. Please handle with caution.

#### **Electrical Characteristics (Ta = 25°C)**

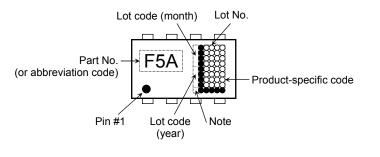
Reverse transfer capacitance $C_{rss}$ $V_{DS} = -10 \text{ V}, V_{QS} = 0 \text{ V}, f = 1 \text{ MHz}$ $ 70$ $ pF$ Output capacitance $C_{oss}$ $V_{DS} = -10 \text{ V}, V_{QS} = 0 \text{ V}, f = 1 \text{ MHz}$ $ 80$ $ 80$ $-$ Switching time $Turn-on time$ $tr$ $V_{GS} = 5 \text{ V}$ $I_D = -1.4 \text{ A}$ $ 5$ $  5$ $-$ Switching time $Turn-on time$ $ton$ $r$ $r$ $r$ $r$ $ 8$ $  8$ $-$ Turn-off time $toff$ $Duty \le 1\%, t_W = 10 \ \mu s$ $ 6$ $  6$ $-$ Total gate charge $Q_{gs}$ $Q_{gs}$ $V_{DD} \simeq -16 \ V, V_{GS} = -5 \ V,$ $ 6$ $  nC$							*		
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Cha	racteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Gate leakage curr	ent	I <sub>GSS</sub>	$V_{GS} = \pm 8 V$ , $V_{DS} = 0 V$	R	14	) ±10	μA	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Drain cut-off curre	nt	I <sub>DSS</sub>	$V_{DS} = -20 V, V_{GS} = 0 V$	$\sim$		-10	μA	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Drain-source brea	kdown voltage	V (BR) DSS	$I_D = -10 \text{ mA}, V_{GS} = 0 \text{ V}$	20	~ _	—	V	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Diam-source brea	Kuowii voltage	V (BR) DSX	$J_{\rm D} = -10$ mA, $V_{\rm GS} = 8$ V	_12	_	—	v	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Gate threshold vol	Itage	V <sub>th</sub>	$V_{DS} = -10 V$ , $I_D = -200 \mu A$	-0.5	_	-1.2	V	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $			RDS (ON)	$V_{GS} = -1.8 \text{ V}, \text{ I}_{D} = -0.7 \text{ A}$	_	215	300		
Forward transfer admittance $V_{fs}$ $V_{DS} = -10 \text{ V}, \text{ I}_{D} = -1.4 \text{ A}$ $2.4$ $4.7$ $-$ SInput capacitance $C_{iss}$ $V_{DS} = -10 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$ $ 470$ $-$ Reverse transfer capacitance $C_{rss}$ $V_{DS} = -10 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$ $ 70$ $ pF$ Output capacitance $C_{oss}$ $ 1_D = -1.4 \text{ A}$ $ 5$ $ 80$ $-$ Switching time $tr$ $tr$ $V_{CS} = 5 \text{ V}$ $I_D = -1.4 \text{ A}$ $ 5$ $ 9$ $-$ Switching time $tr$ $tr$ $V_{CS} = 5 \text{ V}$ $I_D = -1.4 \text{ A}$ $ 8$ $ 70$ $ 9$ $-$ Switching time $tr$ $tr$ $V_{CS} = 5 \text{ V}$ $I_D = -1.4 \text{ A}$ $ 8$ $  8$ $-$ Tum-on time $ton$ $ton$ $V_{CS} = 5 \text{ V}$ $ 8$ $  8$ $-$ Total gate charge $Q_{g}$ $V_{DD} \approx -16 \text{ V}, \text{ V}_{GS} = -5 \text{ V},$ $ 6$ $  -$ Gate-source charge $Q_{gs}$ $V_{DD} \approx -16 \text{ V}, \text{ V}_{GS} = -5 \text{ V},$ $ 6$ $  -$	Drain-source ON r	resistance	R <sub>DS</sub> (ON)	$V_{GS} = -2.5 V_1 D = -1.4 A$		110	160	mΩ	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $			Rps (ON)	$V_{GS} = -4.5 V, I_D = -1.4 A$		72	110		
Reverse transfer capacitance $C_{r_{SS}}$ $V_{DS} = -10$ V, $V_{CS} = 0$ V, $f = 1$ MHz $ 70$ $ pF$ Output capacitance $C_{oss}$ $ 80$ $ 80$ $ 80$ $-$ Switching time $Turn-on time$ $tr$ $V_{CS} = 0$ V, $f = 1$ MHz $ 5$ $  5$ $-$ Switching time $Turn-on time$ $tr$ $V_{CS} = -10$ V $U_{D} = -1.4$ A $ 5$ $  9$ $ 70$ $ 70$ $ 70$ $ 70$ $ 70$ $ 70$ $ 70$ $ 70$ $ 70$ $ 70$ $ 70$ $ 70$ $ 70$ $ 70$ $ 70$ $ 70$ <	Forward transfer a	admittance	Nfs-	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1.4 A	2.4	4.7	—	S	
Output capacitance $C_{OSS}$ $ 80$ $-$ Rise time $t_r$ $I_D = -1.4 \text{ A}$ $ 5$ $-$ Switching time $Turn-on time$ $t_n$ $GS = 5V$ $I_D = -1.4 \text{ A}$ $ 5$ $-$ Switching time $Turn-on time$ $t_n$ $Turn-on time$ $Turn = 10 \text{ µS}$ $ 8$ $  8$ $-$ Total gate charge $Gg$ $V_{DD} \simeq -10 \text{ V}$ $ 26$ $  26$ $-$ Total gate charge $Gg$ $V_{DD} \simeq -16 \text{ V}, \text{ V}_{GS} = -5 \text{ V},$ $ 6$ $  6$ Gate-source charge $Qg_S$ $V_{DD} \simeq -16 \text{ V}, \text{ V}_{GS} = -5 \text{ V},$ $ 4$ $ nC$	Input capacitance	(	Çîsş	$\sim$		470	—		
Rise timetrID = -1.4 ASwitching timeID = -1.4 ATurn-on timeto nFall timetrTurn-off timeto ffTurn-off timeto ffTotal gate chargeO Vout-Total gate chargeO QgVDD $\simeq$ -10 V-Total gate chargeO QgVDD $\simeq$ -16 V, VGS = -5 V,-o CTotal gate charge-o CO Duty<1%, tw = 10 µs-o Co Co C <td colspan="2">Reverse transfer capacitance</td> <td>Crss</td> <td><math>V_{DS} = -10 V</math>, <math>V_{GS} = 0 V</math>, f = 1 MHz</td> <td></td> <td>70</td> <td>—</td> <td>pF</td>	Reverse transfer capacitance		Crss	$V_{DS} = -10 V$ , $V_{GS} = 0 V$ , f = 1 MHz		70	—	pF	
Switching time Turn-on time Fall time Turn-off time Total gate charge (gate-source charge Gate-source charge $Q_{gs}$	Output capacitanc	e 🗍	Coss		_	80	_		
Switching time $t_{f}$ $t_{f}$ $t_{f}$ $t_{g}$ $t_{h}$ $t_{h}$ $t_{g}$ $t_{h}$		Rise time	tr			5			
Fall timetr $C_{H} \neq m$ $n = 0$ $ 8$ $-$ Turn-off-timetoff $Uty \le 1\%$ , $t_W = 10 \ \mu s$ $ 26$ $-$ Total gate charge (gate-source charge $Q_g$ $V_{DD} \simeq -16 \ V$ , $V_{GS} = -5 \ V$ , $I_D = -2.7 \ A$ $ 6$ $-$ Total gate charge (gate-source charge $Q_{gs}$ $V_{DD} \simeq -16 \ V$ , $V_{GS} = -5 \ V$ , $I_D = -2.7 \ A$ $ 6$ $-$	Switching time	Turn-on time	t <sub>on</sub>		_	9		ns	
Turn-off timetoffDuty≤1%, $t_W = 10 \ \mu s$ -26-Total gate charge (gate-source plus gate-drain)Qg $V_{DD} \simeq -16 \ V, \ V_{GS} = -5 \ V,$ -6-Gate-source chargeQg $V_{DD} \simeq -16 \ V, \ V_{GS} = -5 \ V,$ -4-nC		Fall time	tŕ			8		115	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $		Turn-off time	toff		_	26	_		
Gate-source charge $Q_{gs}$ $I_D = -2.7 \text{ A}$ $-4$ $-$	Total gate charge (gate-source plus gate-drain)		$V_{00} \sim -16 V V_{00} = -5 V$		6				
Gate-drain ("miller") charge Q <sub>gd</sub> 2	Gate-source charge		Qgs			4	—	nC	
	Gate-drain ("miller") charge		Q <sub>gd</sub>			2	—		

# Source-Drain Ratings and Characteristics (Ta = 25°C)

Characterist	cs	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse (Note 1)	I <sub>DRP</sub>	—	—	—	-10.8	А
Forward voltage (diode)		V <sub>DSF</sub>	$I_{DR} = -2.7 \text{ A}, \text{ V}_{GS} = 0 \text{ V}$	_	_	1.2	V

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# Marking (Note 6)



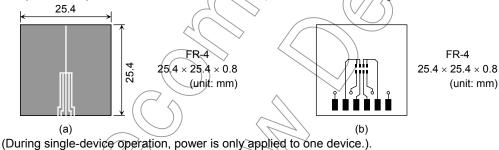
Note: A dot marking for identifying the indication of product Labels. Without a dot: [[Pb]]/INCLUDES > MCV With a dot: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

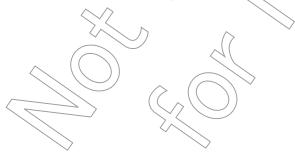
Note 1: Ensure that the channel temperature does not exceed 150°C.

- Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)
- Note 3: a) The power dissipation and thermal resistance values are shown for a single device

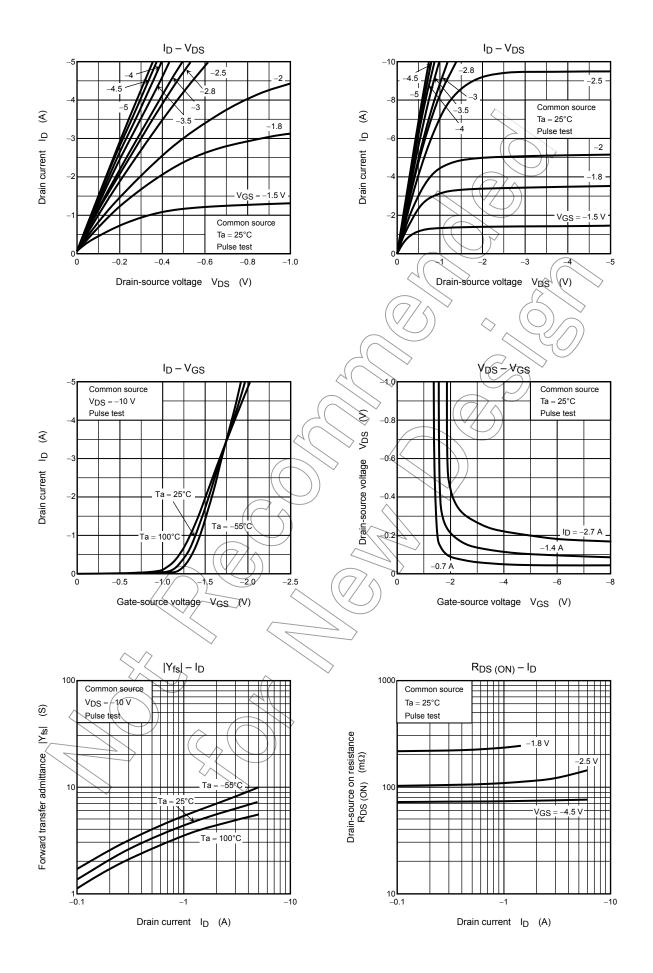


b) The power dissipation and thermal resistance values are shown for a single device.

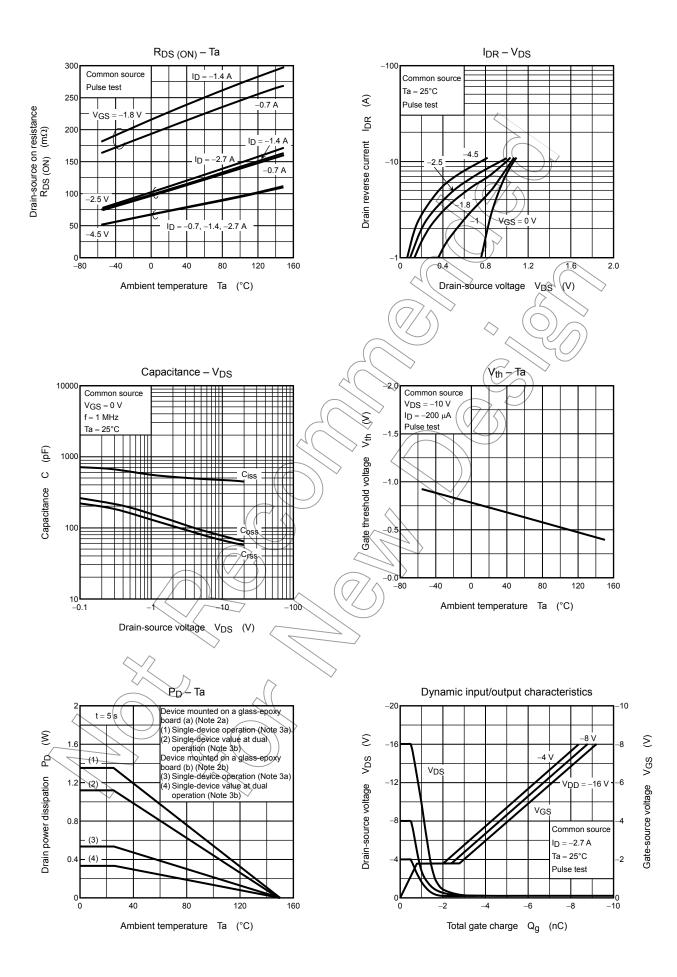
- (During dual operation, power is evenly applied to both devices.).
- Note 4:  $V_{DD} = -16\sqrt{1}, T_{ch} \neq 25^{\circ}C$  (initial), L = 0.5 mH,  $R_G = 25\Omega$ ,  $I_{AR} = -1.35$  A
- Note 5: Repetitive rating: Pulse width limited by maximum channel temperature.
- Note 6: A dot on the lower left of the marking indicates Pin 1

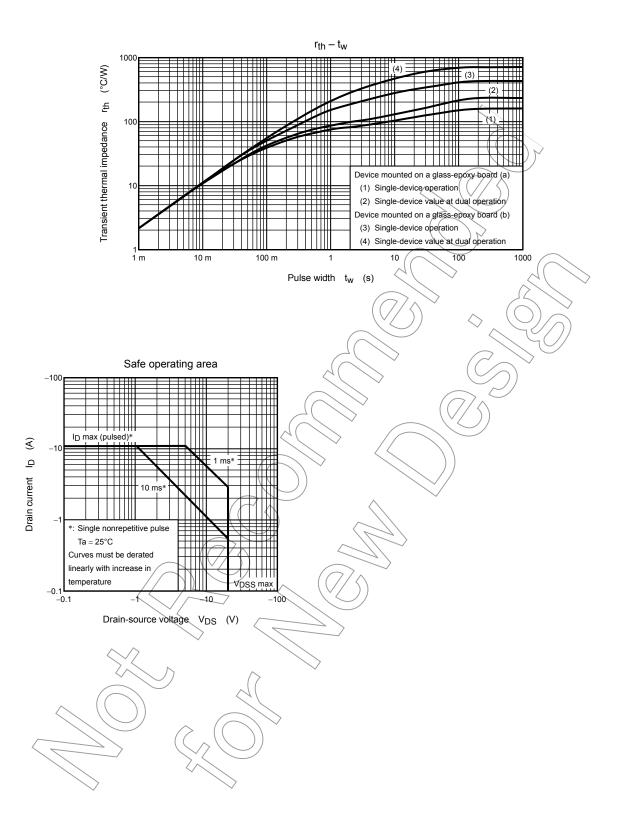


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